

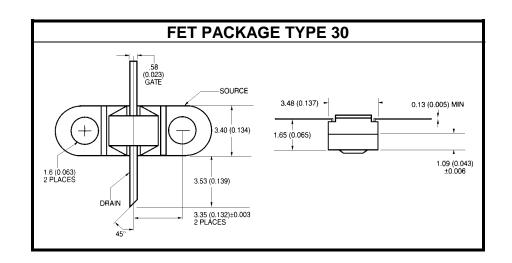
HIGH POWER GaAs FET

FEATURES INCLUDE:

- High Output Power:P1dB = 1.6 W (TYP) @ 12 GHz
- High power gain:GLP = 5 dB (TYP) @ 12 GHz
- High power added efficiency:
 Hadd = 18% (TYP) @ 12 GHz

APPLICATIONS:

S to Ku Band Power Amplifiers



ELECTRICAL SPECIFICATIONS T_A = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
I _{DDS}	SATURATED DRAIN CURRENT $V_{DS} = 3.0 \text{ V}$ $V_{GS} = 0 \text{ V}$	850	1100	1400	mA
V _{GS (off)}	GATE TO SOURCE CUT-OFF VOLTAGE $V_{DS} = 3.0 \text{ V}$ $I_D = 1.0 \text{ mA}$	-2	-3	-5	V